

SMALL SIGNAL NPN TRANSISTOR

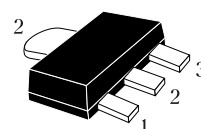
PRELIMINARY DATA

Type	Marking
BF620	620

- SILICON EPITAXIAL PLANAR NPN HIGH VOLTAGE TRANSISTOR
- MINIATURE SOT-89 PLASTIC PACKAGE FOR SURFACE MOUNTING CIRCUITS
- TAPE AND REEL PACKING
- THE PNP COMPLEMENTARY TYPE IS BF621

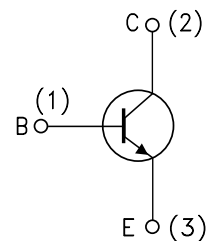
APPLICATIONS

- VIDEO AMPLIFIER CIRCUITS (RGB CATHODE CURRENT CONTROL)
- TELEPHONE WIRELINE INTERFACE (HOOK SWITCHES, DIALER CIRCUITS)



SOT-89

INTERNAL SCHEMATIC DIAGRAM



SC06960

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage ($I_E = 0$)	300	V
V_{CEO}	Collector-Emitter Voltage ($I_B = 0$)	300	V
V_{EBO}	Emitter-Base Voltage ($I_C = 0$)	5	V
I_C	Collector Current	100	mA
I_{CM}	Collector Peak Current	200	mA
P_{tot}	Total Dissipation at $T_C = 25\text{ }^{\circ}\text{C}$	1.2	W
T_{stg}	Storage Temperature	-65 to 150	$^{\circ}\text{C}$
T_j	Max. Operating Junction Temperature	150	$^{\circ}\text{C}$

BF620

THERMAL DATA

$R_{thj-amb}$ •	Thermal Resistance Junction-Ambient	Max	104.1	°C/W
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• Device mounted on a PCB area of 1 cm²

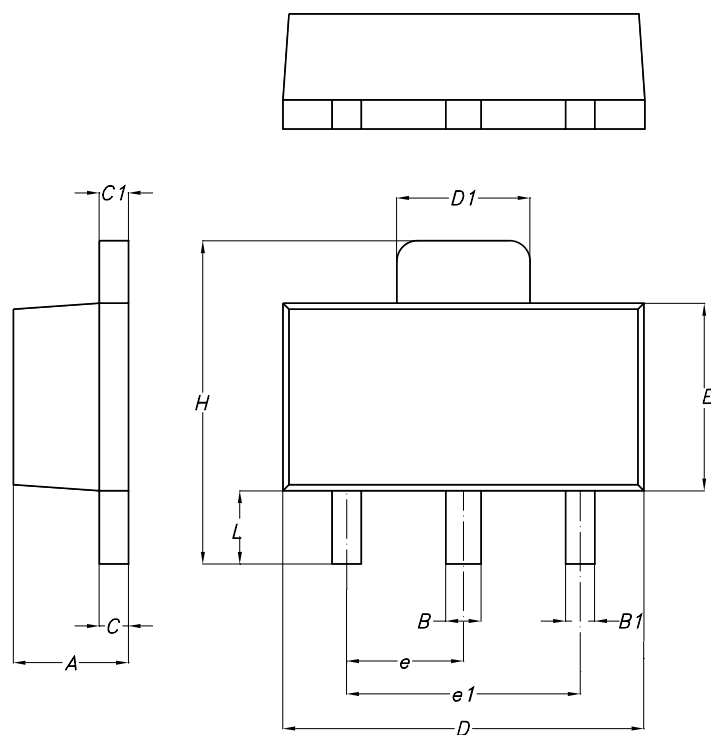
ELECTRICAL CHARACTERISTICS ($T_{case} = 25\text{ °C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	Collector Cut-off Current ($I_E = 0$)	$V_{CB} = 200\text{ V}$ $V_{CB} = 200\text{ V}$ $T_C = 150\text{ °C}$ $V_{CB} = 300\text{ V}$			10 10 100	nA μA μA
I_{EBO}	Emitter Cut-off Current ($I_C = 0$)	$V_{EB} = 5\text{ V}$			50	nA
$V_{(BR)CEO}^*$	Collector-Emitter Breakdown Voltage ($I_B = 0$)	$I_C = 10\text{ mA}$	300			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage ($I_C = 0$)	$I_E = 100\text{ }\mu\text{A}$	5			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 30\text{ mA}$ $I_B = 5\text{ mA}$			0.6	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 30\text{ mA}$ $I_B = 5\text{ mA}$			1.2	V
h_{FE}^*	DC Current Gain	$I_C = 25\text{ mA}$ $V_{CE} = 20\text{ V}$	50			
f_T	Transition Frequency	$I_C = 15\text{ mA}$ $V_{CE} = 10\text{ V}$ $f = 20\text{ MHz}$	60			MHz
C_{CBO}	Collector-Base Capacitance	$I_E = 0$ $V_{CB} = 10\text{ V}$ $f = 1\text{ MHz}$		6		pF
C_{EBO}	Emitter-Base Capacitance	$I_C = 0$ $V_{EB} = 2\text{ V}$ $f = 1\text{ MHz}$		22		pF

* Pulsed: Pulse duration = 300 μs , duty cycle $\leq 2\%$

SOT-89 MECHANICAL DATA

DIM.	mm			mils		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	1.4		1.6	55.1		63.0
B	0.44		0.56	17.3		22.0
B1	0.36		0.48	14.2		18.9
C	0.35		0.44	13.8		17.3
C1	0.35		0.44	13.8		17.3
D	4.4		4.6	173.2		181.1
D1	1.62		1.83	63.8		72.0
E	2.29		2.6	90.2		102.4
e	1.42		1.57	55.9		61.8
e1	2.92		3.07	115.0		120.9
H	3.94		4.25	155.1		167.3
L	0.89		1.2	35.0		47.2



P025H

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